

2SC4835G

Silicon NPN epitaxial planar type

For UHF band low-noise amplification

■ Features

- Low noise figure NF
- High forward transfer gain $|S_{21e}|^2$
- High transition frequency f_T
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

■ Package

- Code
SMini3-F2
- Marking Symbol: 3M
- Pin Name
1: Base
2: Emitter
3: Collector

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	15	V
Collector-emitter voltage (Base open)	V_{CEO}	10	V
Emitter-base voltage (Collector open)	V_{EBO}	2	V
Collector current	I_C	80	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

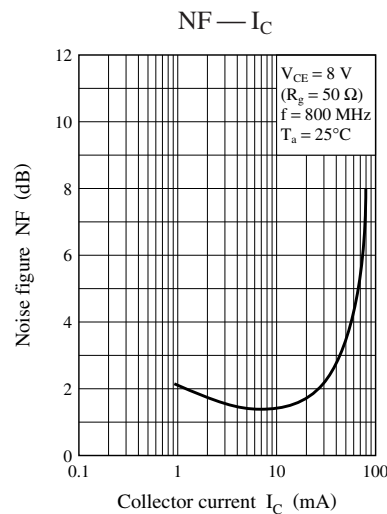
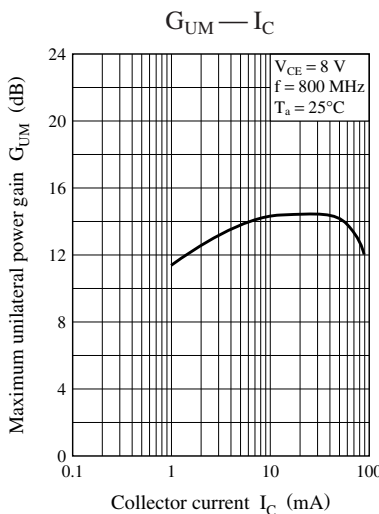
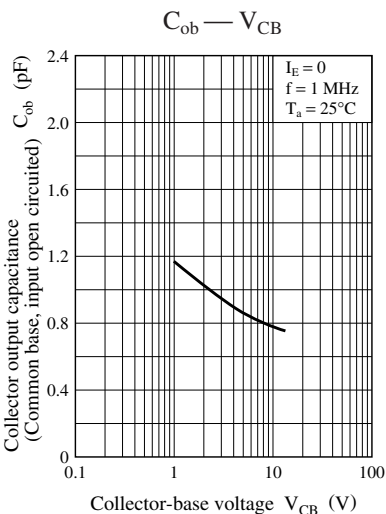
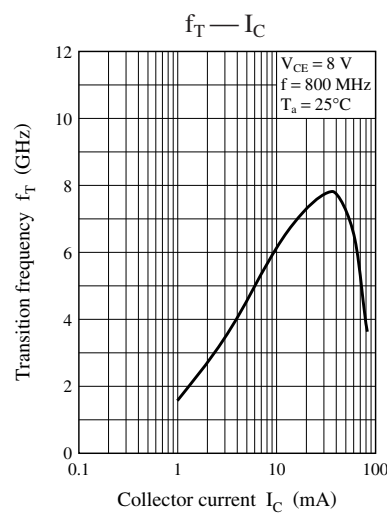
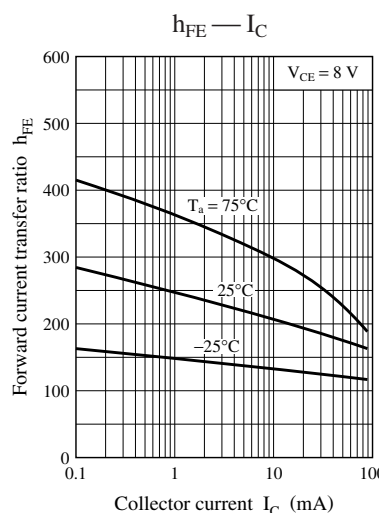
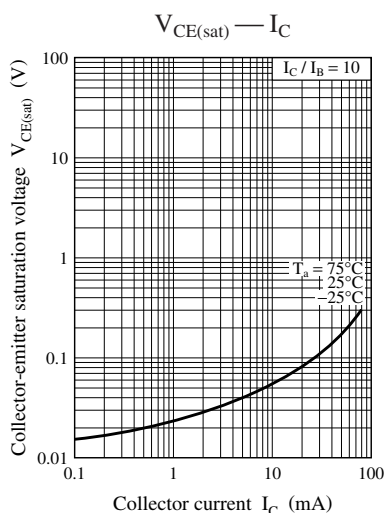
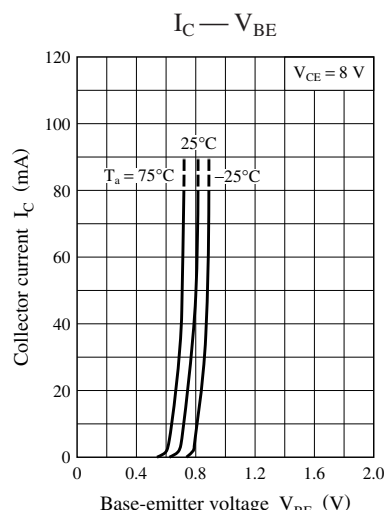
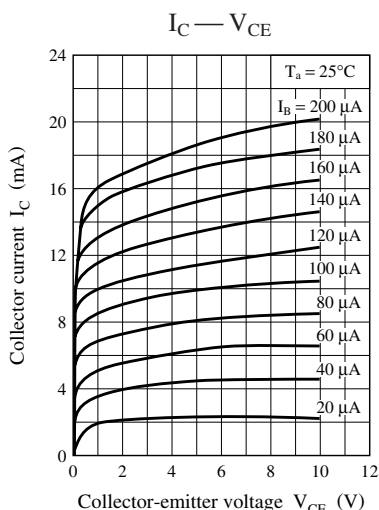
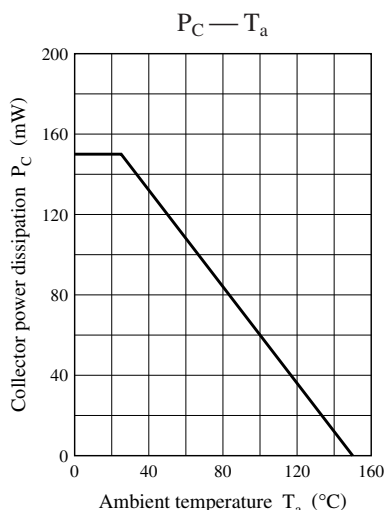
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}$, $I_E = 0$	15			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 100 \mu\text{A}$, $I_B = 0$	10			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10 \text{V}$, $I_E = 0$			1	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 2 \text{V}$, $I_C = 0$			1	μA
Forward current transfer ratio *1,2	h_{FE}	$V_{CE} = 8 \text{V}$, $I_C = 20 \text{mA}$	50		200	—
Transition frequency	f_T	$V_{CE} = 8 \text{V}$, $I_C = 15 \text{mA}$, $f = 800 \text{MHz}$	5	6		GHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = 10 \text{V}$, $I_E = 0$, $f = 1 \text{MHz}$		0.7	1.2	pF
Forward transfer gain	$ S_{21e} ^2$	$V_{CE} = 8 \text{V}$, $I_C = 15 \text{mA}$, $f = 800 \text{MHz}$	11	14		dB
Maximum unilateral power gain	G_{UM}	$V_{CE} = 8 \text{V}$, $I_C = 15 \text{mA}$, $f = 800 \text{MHz}$		15		dB
Noise figure	NF	$V_{CE} = 8 \text{V}$, $I_C = 7 \text{mA}$, $f = 800 \text{MHz}$		1.3	2.0	dB

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

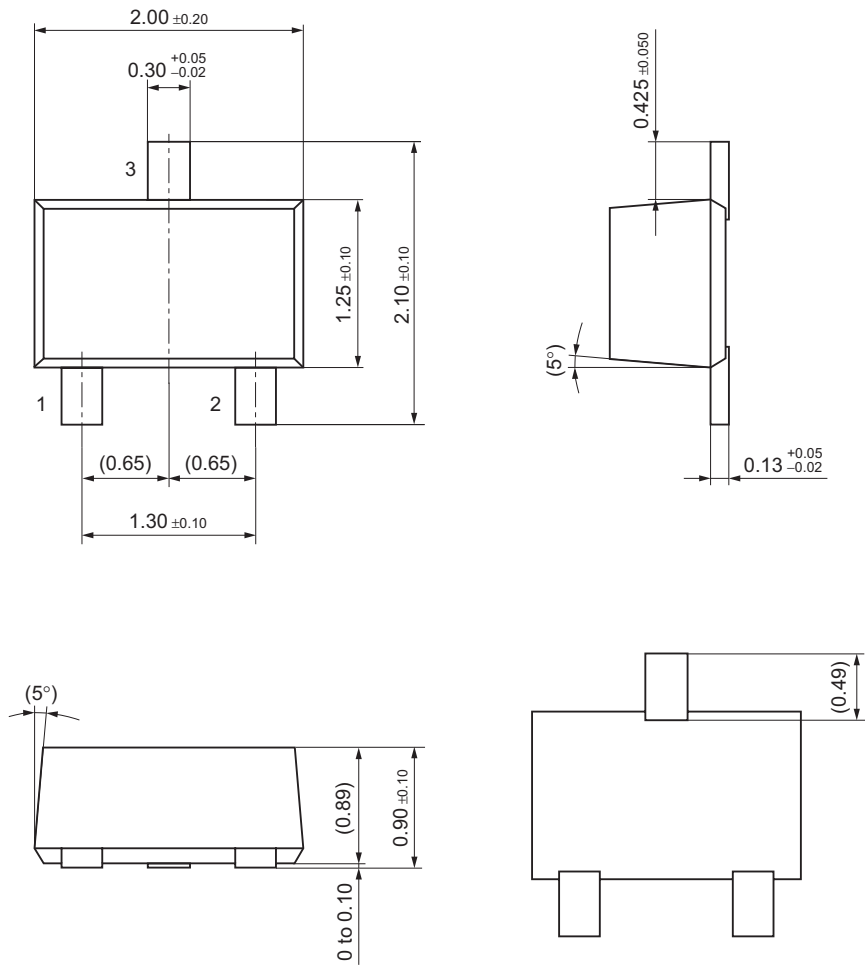
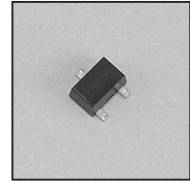
*2: Rank classification

Rank	Q	R	S
h_{FE}	50 to 100	80 to 130	100 to 200



SMini3-F2

Unit: mm



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